

UNISONIC TECHNOLOGIES CO., LTD

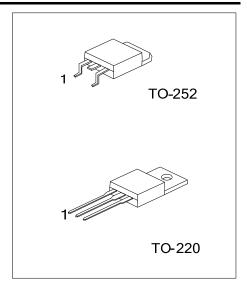
UTT20N10 Power MOSFET

20A, 100V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **UTT20N10** is an N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

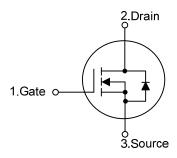
The UTC **UTT20N10** is universally applied in low voltage, such as automotive, high efficiency switching for DC/DC converters, and DC motor control.



■ FEATURES

- * $R_{DS(on)}$ <0.12 Ω @ V_{GS} = 10 V
- * Typically 32pF low C_{RSS}
- * High switching speed
- * Typically 19nC low gate charge

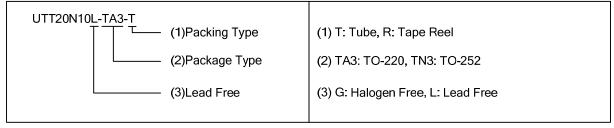
■ SYMBOL



ORDERING INFORMATION

Ordering	Daakana	Pin Assignment			Doolsing		
Lead Free	Halogen Free	Package 1 2		2	3	Packing	
UTT20N10L-TA3-T	UTT20N10G-TA3-T	TO-220	G	D	S	Tube	
UTT20N10L-TN3-R	UTT20N10G-TN3-R	TO-252	G	D	S	Tape Reel	
UTT20N10L-TN3-T	UTT20N10G-TN3-T	TO-252	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ ABSOLUTE MAXIMUM RATINGS (T_c = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ extsf{DSS}}$	100	V
Gate-Source Voltage		V_{GSS}	±25	V
Drain Current	Continuous	I _D	20	Α
	Pulsed	I _{DM}	80	Α
Power Dissipation	TO-220	P _D	62.5	10/
	TO-252		50	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220	θ _{JA}	62.5	°C/W	
	TO-252		100		
Junction to Case	TO-220	θ _{JC}	2	°0/14/	
	TO-252		2.5	°C/W	

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

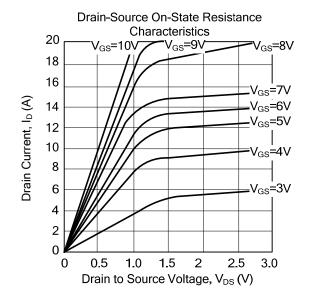
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	100			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μΑ
Gate- Source Leakage Current	Forward	I _{GSS}	V_{GS} =+25V, V_{DS} =0V			+100	nA
	Reverse		V_{GS} =-25V, V_{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =20A			120	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}			600	780	pF
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		165	215	pF
Reverse Transfer Capacitance		C_{RSS}			32	40	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_{G}	V _{GS} =10V, V _{DS} =80V, I _D =19A (Note 1, 2)		19	25	nC
Gate to Source Charge		Q_{GS}			3.9		nC
Gate to Drain Charge		Q_GD	(Note 1, 2)		9.0		nC
Turn-ON Delay Time		$t_{D(ON)}$			7.5	25	ns
Rise Time		t_R	V_{DD} =50V, I_D =1A, R_L =50 Ω ,		150	310	ns
Turn-OFF Delay Time		$t_{D(OFF)}$	V_{GS} =10V, R_G =25 Ω (Note 1, 2)		20	50	ns
Fall-Time		t_{F}			65	140	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuou	is Current	Is				20	Α
Maximum Body-Diode Pulsed Current		I _{SM}				80	Α
Drain-Source Diode Forward Voltage		V _{SD}	I _S =20A, V _{GS} =0V			1.5	V

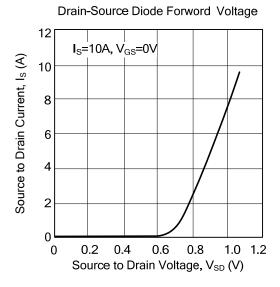
Notes: 1. Pulse Test: Pulse width≤300µs, Duty cycle≤2%

2. Essentially independent of operating temperature

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■ TYPICAL CHARACTERISTICS





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